

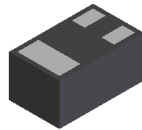
Features

- Low Collector-Emitter Saturation Voltage, $V_{CE(sat)}$
- Ultra-Small Leadless Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

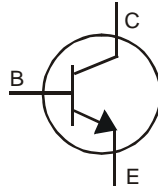
Mechanical Data

- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0009 grams (Approximate)

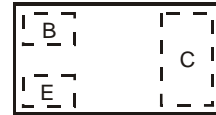
X2-DFN1006-3



Bottom View



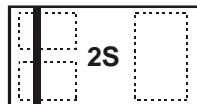
Device Symbol


 Top View
Device Schematic

Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT2222ALP4-7B	2S	7	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information


Top View

2S = Product Type Marking Code
Bar Denotes Base and Emitter Side

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current - Continuous	I_C	600	mA
Peak Collector Current	I_{CM}	800	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	460	mW
Power Dissipation (Note 6)	P_D	1	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	272	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	120	$^\circ\text{C/W}$
Thermal Resistance, Junction to Lead (Note 7)	$R_{\theta JL}$	110	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	$\geq 8,000$	V	3B
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

- Notes:
- For a device surface mounted on minimum recommended pad layout FR-4 PCB with single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The entire exposed collector pad is attached to the heatsink.
 - Same as note 5, except device is surface mounted on 25mm X 25mm collector pad heatsink with 1oz copper.
 - Thermal resistance from junction to solder-point (at the end of the collector lead).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics

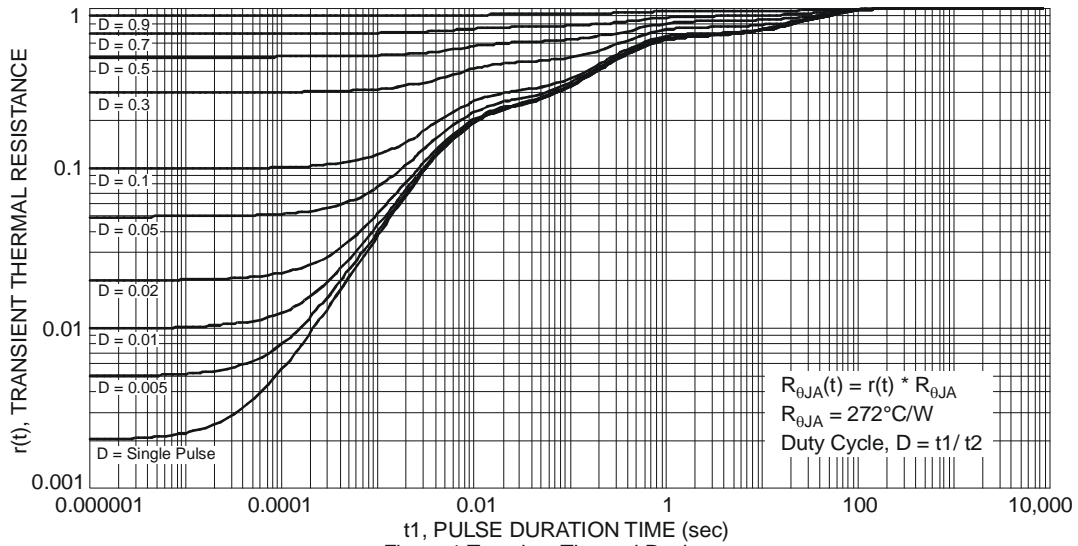


Figure 1 Transient Thermal Resistance

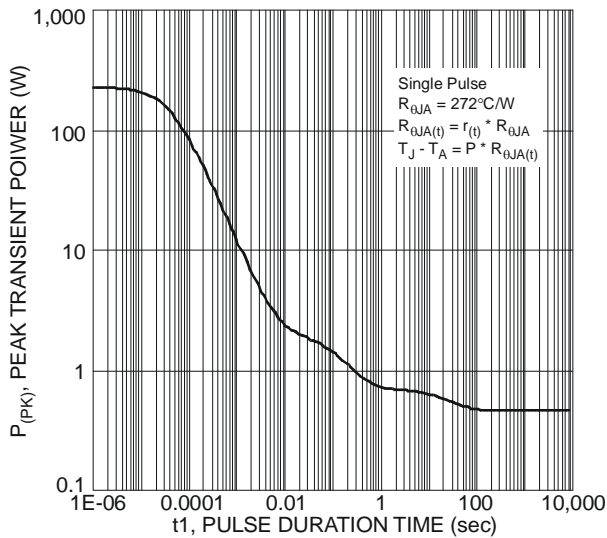


Figure 2 Single Pulse Maximum Power Dissipation

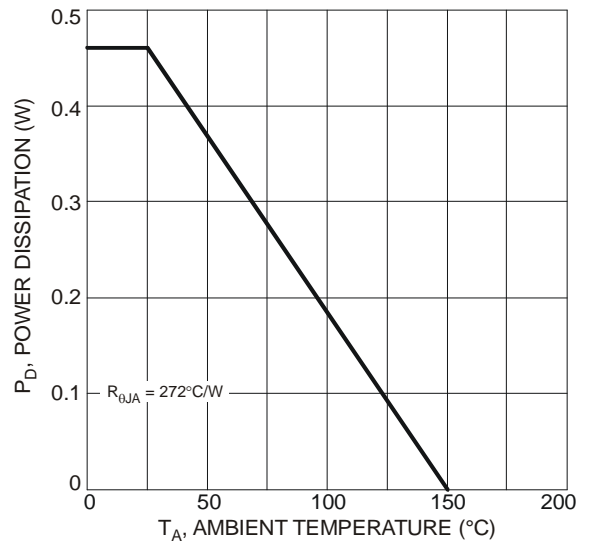


Figure 3 Power Dissipation vs. Ambient Temperature

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CB0}	75	—	—	V	I _C = 100μA, I _E = 0
Collector-Emitter Breakdown Voltage (Note 6)	BV _{CEO}	40	—	—	V	I _C = 10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	6	—	—	V	I _E = 100μA, I _C = 0
Collector Cutoff Current	I _{CEX}	—	—	10	nA	V _{CE} = 60V, V _{EB(off)} = 3V
Collector Cutoff Current	I _{CB0}	—	—	10	nA	V _{CB} = 60V, I _E = 0
		—	—	10	μA	V _{CB} = 60V, I _E = 0, T _A = +125°C
Emitter Cutoff Current	I _{EBO}	—	—	10	nA	V _{EB} = 5V, I _C = 0
Base Cutoff Current	I _{BL}	—	—	20	nA	V _{CE} = 60V, V _{EB(off)} = 3V
ON CHARACTERISTICS (Note 6)						
DC Current Gain	h _{FE}	35	—	—	—	V _{CE} = 10V, I _C = 0.1mA
		50	—	—	—	V _{CE} = 10V, I _C = 1mA
		75	—	—	—	V _{CE} = 10V, I _C = 10mA
		35	—	—	—	V _{CE} = 10V, I _C = 10mA, T _A = -55°C
		100	—	300	—	V _{CE} = 10V, I _C = 150mA
		50	—	—	—	V _{CE} = 1V, I _C = 150mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	—	0.3	V	I _C = 150mA, I _B = 15mA
		—	—	1.0	V	I _C = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.6	—	1.2	V	I _C = 150mA, I _B = 15mA
		—	—	2.0	V	I _C = 500mA, I _B = 50mA
SMALL SIGNAL CHARACTERISTICS (Note 6)						
Output Capacitance	C _{obo}	—	—	8	pF	V _{CB} = 10V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{ibo}	—	—	25	pF	V _{EB} = 0.5V, f = 1.0MHz, I _C = 0
Current Gain-Bandwidth Product	f _T	300	—	—	MHz	V _{CE} = 20V, I _C = 20mA, f = 100MHz
Noise Figure	NF	—	—	4.0	dB	V _{CE} = 10V, I _C = 100μA, R _S = 1.0kΩ, f = 1.0kHz
Input Impedance	h _{ie}	0.25	—	1.25	kΩ	I _C = 10mA, V _{CE} = 10V, f = 1.0kHz
Voltage Feedback Ratio	h _{re}	—	—	4.0	X 10 ⁻⁴	
Small-Signal Current Gain	h _{fe}	75	—	375	—	
Output Admittance	h _{oe}	25	—	200	μS	
SWITCHING CHARACTERISTICS (Note 6)						
Delay Time	t _d	—	—	10	nS	V _{CC} = 30V, V _{BE(off)} = -0.5V, I _C = 150mA, I _{B1} = 15mA
Rise Time	t _r	—	—	25		
Storage Time	t _s	—	—	225		
Fall Time	t _f	—	—	60		

Notes: 6. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

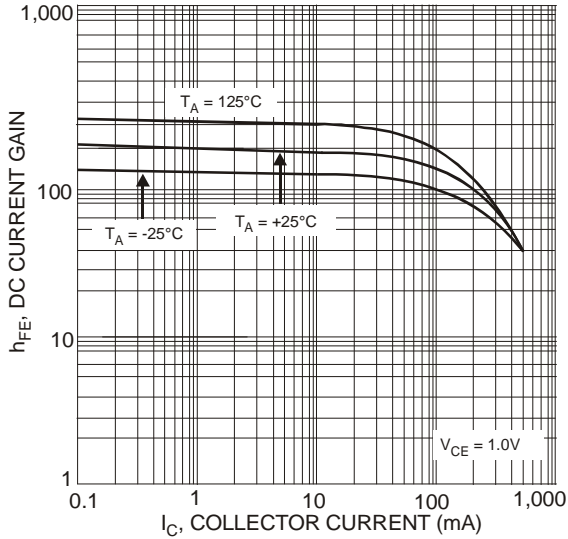


Figure 4 Typical DC Current Gain vs. Collector Current

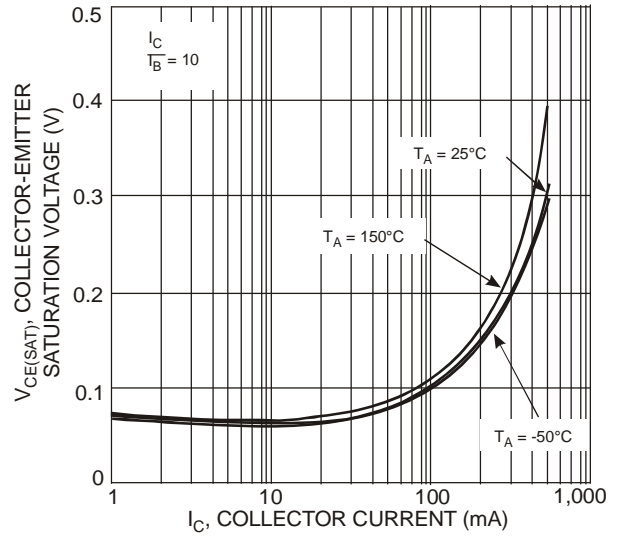


Figure 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current

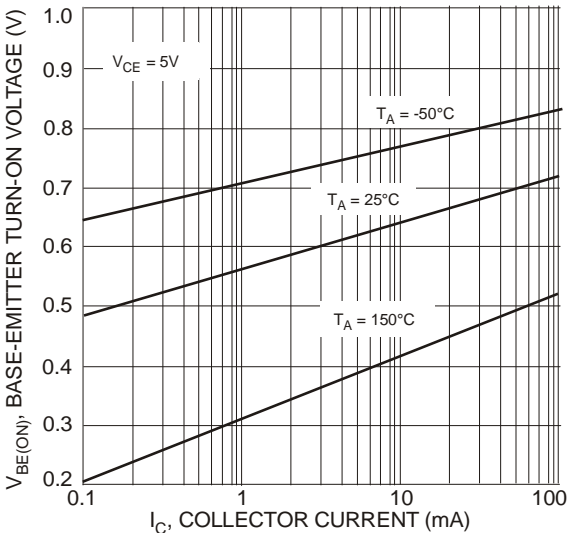


Figure 6 Typical Base-Emitter Turn-On Voltage vs. Collector Current

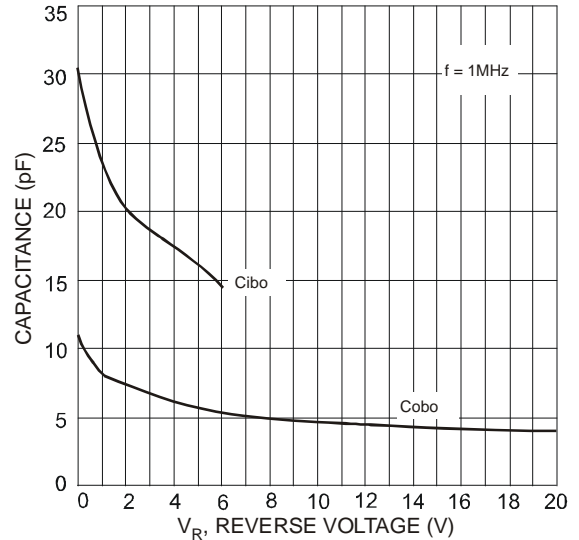


Figure 7 Typical Capacitance Characteristics

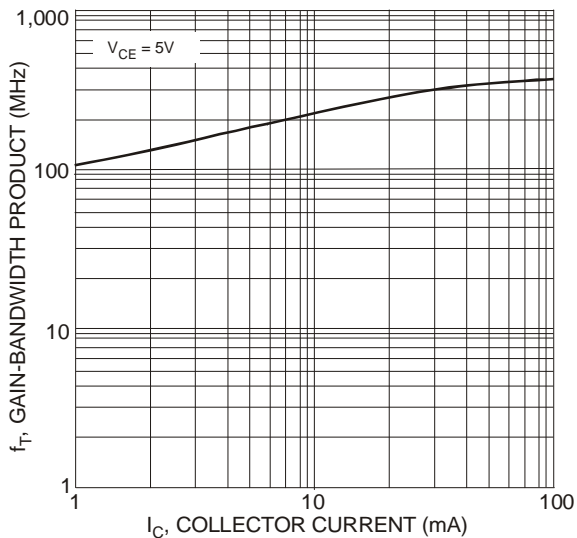


Figure 8 Typical Gain-Bandwidth Product vs. Collector Current

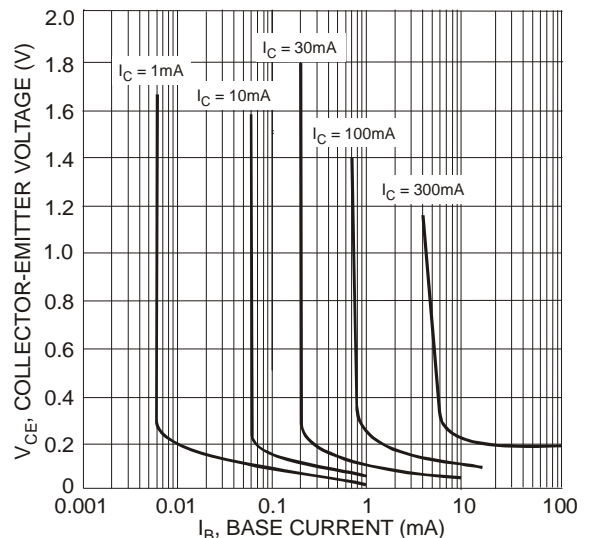
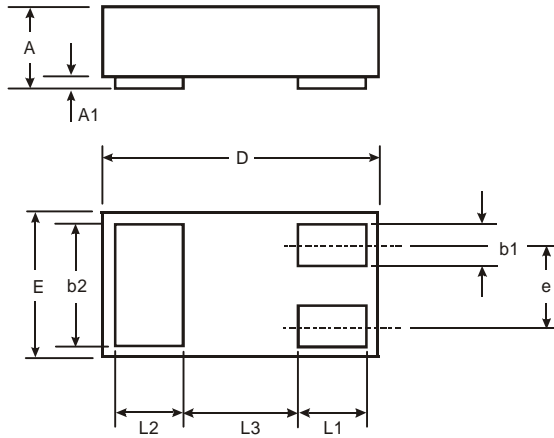


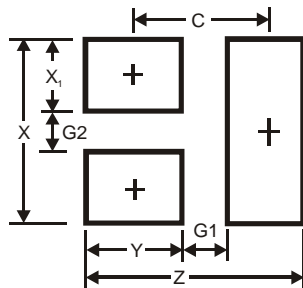
Figure 9 Typical Collector Saturation Region

Package Outline Dimensions



X2-DFN1006-3			
Dim	Min	Max	Typ
A	—	0.40	—
A1	0	0.05	0.03
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.05	1.00
E	0.55	0.65	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	—	—	0.40
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
C	0.7

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